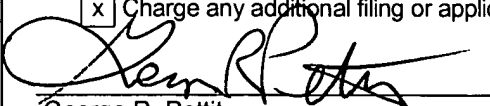


AF 12822



AMENDMENT TRANSMITTAL LETTER				Docket No. 21776-00039-US	
Application No. 09/387,857-Conf. #3099		Filing Date September 1, 1999		Examiner C. Novacek	
				Art Unit 2822	
Applicant(s): Fumitaka Sugaya					
Invention: A SEMICONDUCTOR DEVICE AND A METHOD OF MANUFACTURING THE SAME					
TO THE COMMISSIONER FOR PATENTS					
Transmitted herewith is an amendment in the above-identified application.					
The fee has been calculated and is transmitted as shown below.					
CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	18	- 20 =	0	x	0.00
Independent Claims	5	- 5 =	0	x	0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00
<input checked="" type="checkbox"/> Large Entity <input type="checkbox"/> Small Entity					
<input checked="" type="checkbox"/> No additional fee is required for this amendment.					
<input type="checkbox"/> Please charge Deposit Account No. <u>22-0185</u> in the amount of \$ _____. A duplicate copy of this sheet is enclosed.					
<input type="checkbox"/> A check in the amount of \$ _____ to cover the filing fee is enclosed.					
<input type="checkbox"/> Payment by credit card. Form PTO-2038 is attached.					
<input checked="" type="checkbox"/> The Commissioner is hereby authorized to charge and credit Deposit Account No. <u>22-0185</u> as described below. A duplicate copy of this sheet is enclosed.					
<input checked="" type="checkbox"/> Credit any overpayment.					
<input checked="" type="checkbox"/> Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.					
 George R. Pettit Attorney Reg. No.: 27,369 CONNOLLY BOVE LODGE & HUTZ, LLP 1990 M Street, N.W., Suite 800 Washington, DC 20036-3425 (202) 331-7111				Dated: <u>11-25-02</u>	

 NOV 29 2002
 TECHNOLOGY CENTER 2800

RECEIVED



~~Do not enter~~
OK 12/11/02

Docket No.: 21776-00039-US
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Conf. No. 3099

Fumitaka Sugaya

Application No.: 09/387,857

Group Art Unit: 2822

Filed: September 1, 1999

Examiner: C. Novacek

For: A SEMICONDUCTOR DEVICE AND A
METHOD OF MANUFACTURING THE
SAME

11/15 And 12/13/02
A. J. J. J.
1/23/03

AMENDMENT UNDER 37 CFR 1.116

Box AF
Commissioner for Patents
Washington, DC 20231

RECEIVED
NOV 29 2002
TECHNOLOGY CENTER 2800

Dear Sir:

In response to the Final Rejection mailed August 23, 2002 (Paper No. 10), please amend the above-identified U.S. patent application as follows:

IN THE CLAIMS:

Kindly amend the claims as follows:

DI

32. (Amended) A method of fabricating a semiconductor device, comprising:

the first step of defining an element active region by forming an element isolation structure on a semiconductor substrate;

the second step of forming a gate insulating film and a gate electrode in said element active region;

the third step of doping an impurity into said active region of said substrate to form a pair of impurity diffusion layers in surface regions of said semiconductor substrate on two sides of said gate electrode;